



Optical properties of ultrathin Al₂O₃/ZnO nanolaminates



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ABSTRACT

Because of their high resistance against ultraviolet and high energy particles, ultrathin amorphous nanolaminates can be very attractive for aerospace application. Here we report on the optical and structural properties of ultrathin Al₂O₃/ZnO nanolaminates deposited by Atomic Layer Deposition. Structural properties of nanolaminates were studied by GIXRD and AFM. Optical characterization was performed by transmittance, spectroscopic ellipsometry and photoluminescence (PL) spectroscopy. Regression analysis of ellipsometric spectra has shown that absorption peak decreases and blue shifted with the decrease of bilayer thickness in the stack. On the basis of the analysis of structural and optical properties of ultrathin nanolaminates, the amorphous nature of them is suggested.

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1. Introduction

Nowadays a new class of materials based on nanostructures is started to be used for innovative optical elements, [1] photovoltaic, energy storage devices [2] and temperature sensitive substrates for biosensors [3–6]. Nanolaminates have been applied for aerospace application as thin shell mirrors. Because of their high resistance against ultraviolet irradiation and high energy particles, ultrathin nanolaminates can be very attractive when amorphous structures are achieved [7].

It is well known that bulk and thin films of hundreds of nanometers of zinc oxide deposited on various substrates most frequently generate an anisotropic optical response to incident electromagnetic field. A number of publications have been dedicated for studies of anisotropic ZnO dielectric function in deep-ultra-violet, ultra-violet, visible and infrared regions [8]. However, ZnO layers with hexagonal crystal structure do not have necessary mechanical and optical features for advanced applications in the fields mentioned above. For this purpose, zinc oxide nanolaminates (about 2 nm and less) are one of the most prospective materials for such applications because their amorphous structures.

Optical methods such as transmittance-reflection spectroscopy, spectroscopic ellipsometry (SE) and photoluminescence spectroscopy (PL) can be very useful to characterize the structure of ultrathin nanolaminates. Transmittance-reflection spectroscopy indicates the changes of absorption for different thicknesses of nanolaminates bilayers. Optical dispersion of refractive index of ultrathin ALD deposited nanolaminates can determine optical parameters of individual layers in multilayered ultrathin structures. Large interface sensitivity of SE enables us to analyze in detail the structure and properties of ultrathin layers [9]. Spectra of PL give information about excitonic peak position and amplitude which is the indication of level of ordering in ZnO layers. They demonstrate room temperature photoluminescence in UV and visible range, corresponding to near band and defect level emission, respectively.

In the present work the optical methods studies have been carried out on ultrathin nanolaminates of Al₂O₃/ZnO layers (lower than 20 nm). The determined optical parameters of nanolaminates were analyzed in order to reveal amorphous structure of ultrathin ZnO layers. The most of attention was paid to absorption changes of transmittance and ellipsometric spectra with bilayers thickness decreasing in nanolaminates. The reasons of the observed effect were discussed. Here we focus more on the characterization of nanolaminates by spectroscopic optical methods such as optical transmission-reflection, spectroscopic ellipsometry and photoluminescence. We want to show that from spectroscopic optical methods, we can reliably characterize

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Table 1

Thickness of ZnO single thin film and Al₂O₃/ZnO ultrathin nanolaminates synthesis by ALD.

Samples	Cycles of Al ₂ O ₃	Cycles of ZnO	Numbers of bilayers	Bilayer thickness (nm)
Al ₂ O ₃ /ZnO 20 (0.6/0.6 nm)	3	3	20	1.2
Al ₂ O ₃ /ZnO 10 (1/1 nm)	5	5	10	2
Al ₂ O ₃ /ZnO 4 (2.6/2.6 nm)	13	13	4	5.2
Al ₂ O ₃ /ZnO 2 (5/5 nm)	25	25	2	10
Al ₂ O ₃ /ZnO 1 (10/10 nm)	50	50	1	20

the transition from crystalline to amorphous structures and evaluate the degree of disorder.

2. Experimental details

2.1. Materials

Diethyl Zinc (DEZ) (Zn(CH₂CH₃)₂, 95% purity, CAS: 557-20-0) and Trimethylaluminum (TMA) ((CH₃)₃Al) 98% purity, CAS: 75-24-1) were obtained from Sigma Aldrich. Silicon wafer p-type (100) and glass substrates were purchased from MEMC Korea Company and RS France respectively.

2.2. Synthesis of Al₂O₃/ZnO ultrathin nanolaminates

Silicon and glass substrates were pre-cleaned in acetone, ethanol and deionized water. A custom made ALD reactor was used for the synthesis of ultrathin Al₂O₃/ZnO nanolaminates. ALD was performed using sequential exposures of TMA (DEZ) and H₂O separated by a purge of

argon with a flow rate of 100 sccm. The deposition regime for ZnO and Al₂O₃ consisted of 0.1 s pulse of TMA (DEZ), 30 s of exposure to TMA (DEZ), 30 s of purge with argon followed by 2 s pulse of H₂O, 30 s of exposure to H₂O and finally 40 s purge with argon. Al₂O₃/ZnO ultrathin nanolaminates with different number of cycles were deposited both on Si substrates and glass substrates by ALD (Table 1), the temperature was fixed to 100 °C.

2.3. Characterization

Structural properties of Al₂O₃/ZnO nanolaminates were characterized using Grazing Incidence X-ray Diffraction (GIXRD; Bruker D5000). BioScope Catalyst (Bruker, USA) atomic force microscope in contact mode was used for the evaluation of surface morphology. Sharpened silicon nitride tip (spring constant – 0.35 N/m, resonant frequency – 65 kHz) was employed. Surface roughness was calculated using NanoScope 8.10 software.

Optical properties of ultrathin nanolaminates have been studied by photoluminescence spectroscopy in the spectral range 370–800 nm. The excitation of luminescence was performed by a solid state laser source (Nd:YAG, LCS-DTL-374QT, Russia, 355 nm, 13 mW/cm²). The registration of the emitted spectra was provided by an experimental setup described elsewhere [10,11].

All spectroscopic ellipsometry measurements were carried from 210 nm to 1000 nm wavelength using J. A. Woollam spectral ellipsometer M-2000× with a rotating compensator. Measurements of nanolaminates were performed at fixed angle of incident light 70°. For calculation of optical constants Complete Ease software from J. A. Woollam was used. Measurement procedure was performed in the same way as in our previous work [11].

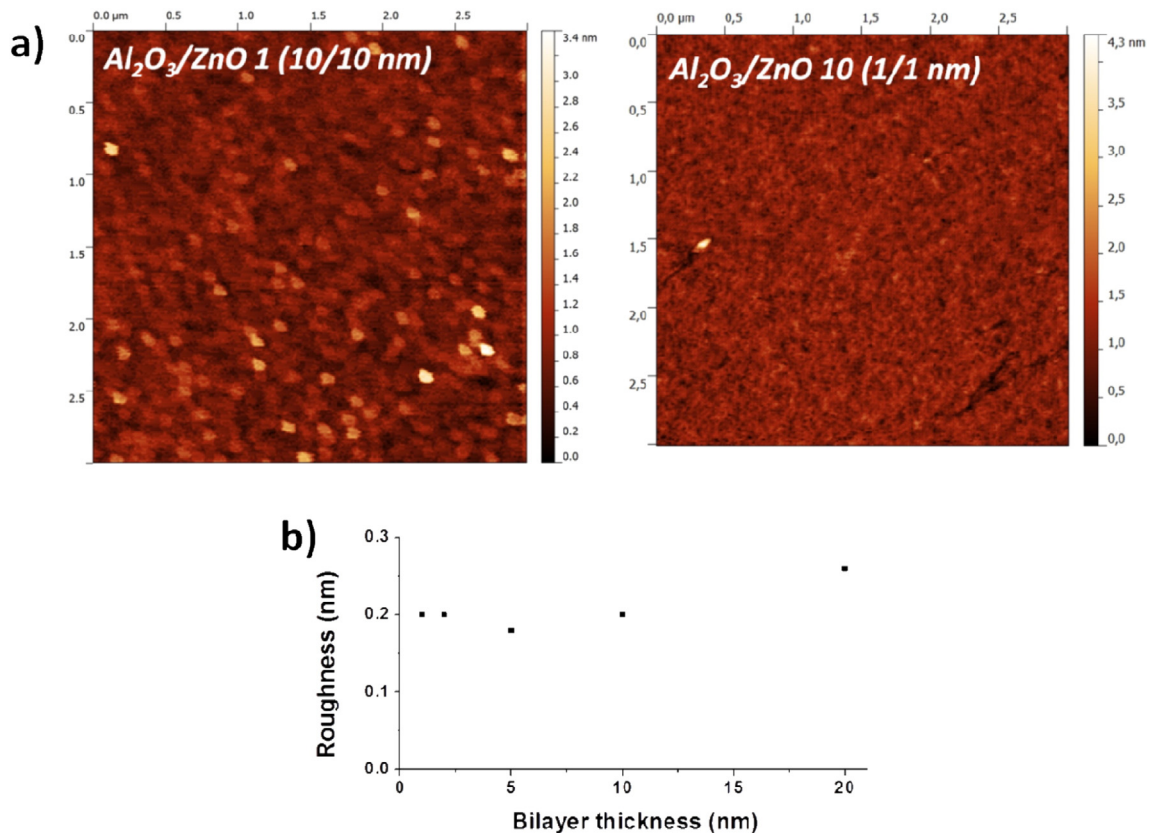


Fig. 1. (a) AFM images of Al₂O₃/ZnO nanolaminates with different bilayer thicknesses; the image size is 3 μm × 3 μm and the height scale is 4 nm; (b) roughness vs the bilayers thickness in the Al₂O₃/ZnO ultrathin nanolaminates.

3. Results and discussion

$\text{Al}_2\text{O}_3/\text{ZnO}$ ultrathin nanolaminates (about 20 nm total thickness) with different bilayers thicknesses were deposited both on Si substrates and glass substrates by ALD (Table 1). In all ultrathin nanolaminates, the first layer on Si substrate was Al_2O_3 and the top layer of the nanolaminate was ZnO. The growth rates of Al_2O_3 and ZnO in the nanolaminates vary between 1.4 to 2 Å per cycle and 1.8 to 2 Å per cycle respectively as it has been determined elsewhere. In our previous study on structural and mechanical properties of $\text{Al}_2\text{O}_3/\text{ZnO}$ nanolaminates, [12] we demonstrated that with bilayer spacing of 2.5 nm, the ZnO film becomes fully amorphous. Transition from crystalline to amorphous structure with the decrease of bilayer spacing was demonstrated by TEM and GIXRD [10,11,13].

Surface morphology of the samples studied using AFM is shown in Fig. 1. Ultrathin film of 20 nm thickness showed smooth surface with insignificant surface roughness. The root mean square (rms), calculated from AFM data, showed no clear dependence on the bilayers thickness up to 10 nm. A little decrease of the rms is observed when we reduce the bilayers thickness from 20 to 10 nm. After, the rms remains constant when decreasing the bilayers thickness from 10 to 1.2 nm. As reported elsewhere [10,11,13], amorphous Al_2O_3 blocks the ZnO crystal growth and forces the ZnO to renucleate on the Al_2O_3 surface. It should be noted that the surface roughness of nanolaminates was lower than that for 20 nm thick ZnO [10]. Transmittance spectra (Fig. 2) showed that all measured samples deposited on glass substrate were transparent in the range of 450–1100 nm. Nanolaminates with bilayer thickness of 1.2 nm and 2 nm did not show significant absorbance. Thus, it was

difficult to distinguish ZnO absorbance from the substrate absorbance. The band gap value was calculated for samples with bilayer thickness of 20, 10 and 5.2 nm using the observed absorption edge.

Absorption coefficient α is related to the transmittance of the sample T as [10,11]:

$$\alpha \cdot d = \ln\left(\frac{1}{T}\right) \quad (1)$$

where d is a thickness of the sample.

In order to simplify the calculation of the band gap values of the nanolaminates, an optical density OD ($OD = \alpha \times d$) was used [10,11].

The band gap value of the samples was calculated considering that Al_2O_3 is totally transparent and the observed absorption edge is related to ZnO layers. ZnO is known as a semiconductor with direct optical transitions. Therefore, the absorption coefficient α can be described by the following equation [10,11]:

$$\alpha = \frac{(h\nu - E_g)^{1/2}}{h\nu} \quad (2)$$

where $h\nu$ and E_g are a photon energy and a band gap values, respectively.

Considering Eqs. (1) and (2), from the plot $(OD \times hv)^2$ vs $h\nu$ band gap values E_g were graphically determined (Fig. 2b) in linear part of the absorption edge with respect to Eq. (2) and summarized in Table 2.

SE measurements were performed in order to determine optical dispersion of refractive index and extinction coefficient for $\text{Al}_2\text{O}_3/\text{ZnO}$ nanolaminates. SE data for $\text{Al}_2\text{O}_3/\text{ZnO}$ nanolaminates were analyzed by the multi-layer model [11]. In this study multi-layer model represented the structure of nanolaminates consisted from bilayers of $\text{Al}_2\text{O}_3/\text{ZnO}$. The Bruggeman effective media approximation was used to determine the fraction volume of Al_2O_3 and ZnO in the bilayers. The starting values of ZnO and Al_2O_3 optical dispersion was taken from “Complete Ease” software database. Single ZnO layer deposited on Si substrate with thickness of 250 nm was characterized by Critical Point Parabolic Band function [14]. This function is related to the electronic band-to-band transitions. Al_2O_3 optical constants in ultrathin nanolaminates were described using Cauchy dispersion function. The regression analysis was made by fixing the thickness of the stack layer of nanolaminate (20 nm) meanwhile coefficients in optical dispersion functions and volume fractions in bilayers were free fitting parameters. The mean square error (MSE) of nanolaminates modeling was from 7.3 to 23. The effective optical constants of nanolaminates differ depending on the bilayer thickness (Fig. 3). For comparison of refractive index values, the upper ZnO layers were taken. It can be seen, that the refractive index of ZnO decreases with the decrease of the single layer thickness in the range of 10 to 2.6 nm. The obtained results were compared with refractive index of 250 nm ZnO single layer, deposited on Si substrate. The decrease of ZnO refractive index, deposited on Al_2O_3 could be related to the change of the growth and the increase of the density of the deposited layers [11]. No constituent increase of refractive index was observed for nanolaminates with single ZnO layer thickness of 1 and 0.6 nm.

The extinction coefficients and band gap values have been used in order to analyze structural changes of nanolaminates depending on bilayers spacing obtained from SE and optical transmittance spectra.

Table 2

Band gap and Urbach energy of $\text{Al}_2\text{O}_3/\text{ZnO}$ nanolaminates with different bilayer thicknesses.

Samples	E_g (eV) from transmittance	E_g (eV) from SE	Urbach energy (eV)
$\text{Al}_2\text{O}_3/\text{ZnO}$ 20 (0.6/0.6 nm)	–	3.45	0.638623
$\text{Al}_2\text{O}_3/\text{ZnO}$ 10 (1/1 nm)	–	3.42	0.473774
$\text{Al}_2\text{O}_3/\text{ZnO}$ 4 (2.6/2.6 nm)	3.3	3.38	0.215752
$\text{Al}_2\text{O}_3/\text{ZnO}$ 2 (5/5 nm)	3.25	3.39	0.062589
$\text{Al}_2\text{O}_3/\text{ZnO}$ 1 (10/10 nm)	3.24	3.35	0.0826

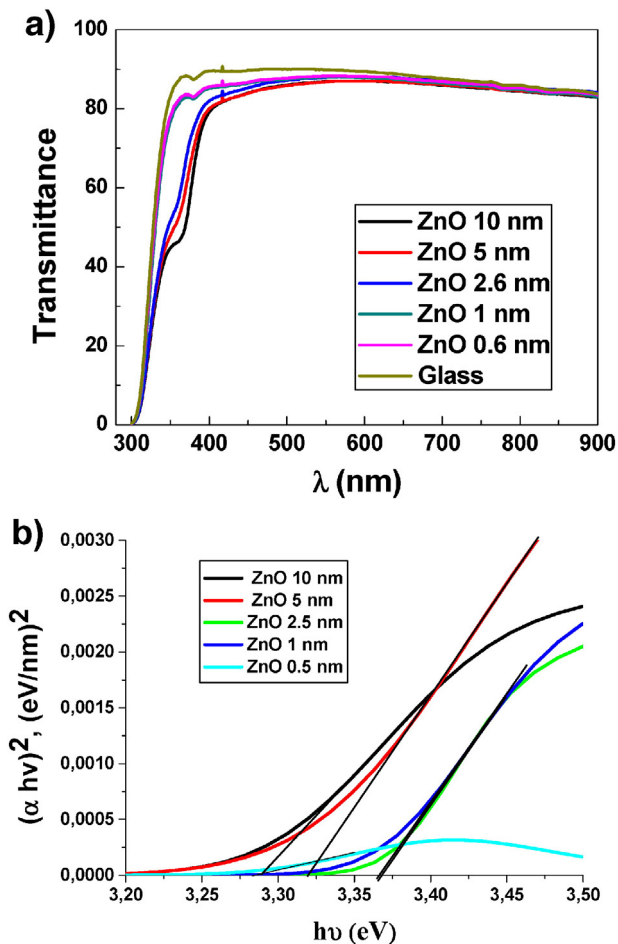


Fig. 2. a) Transmission spectra of $\text{Al}_2\text{O}_3/\text{ZnO}$ nanolaminates with different bilayer thicknesses and (b) bandgap extraction from the plot of $(\alpha h\nu)^2$ as a function of photon energy ($h\nu$).

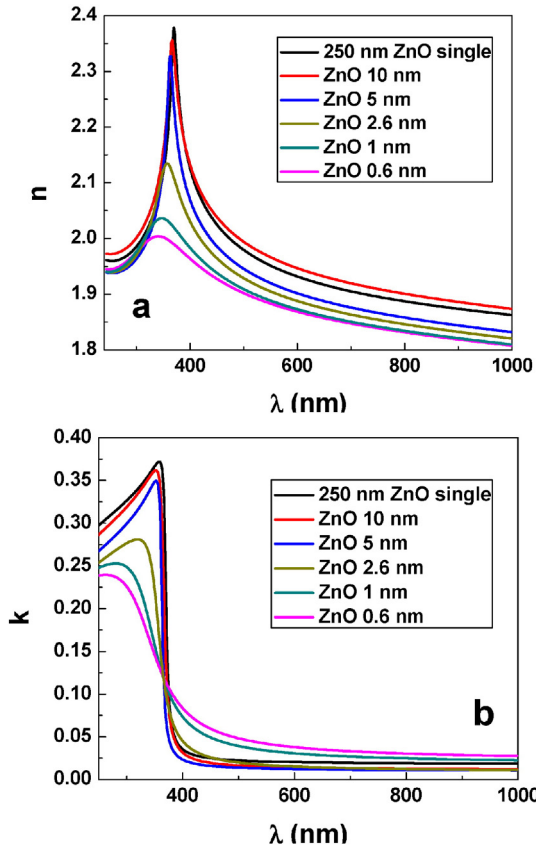


Fig. 3. Spectra of refractive index (a) and extinction coefficient (b) of ZnO single layers in Al₂O₃/ZnO nanolaminates with different bilayer thicknesses obtained by regression analysis of ellipsometric data.

To evaluate the band gap values, extinction coefficients of the top ZnO single layer were used. Extinction and absorption coefficients are related through following equation [11]:

$$\alpha = \frac{4 \cdot \pi \cdot k}{\lambda} \quad (3)$$

where α , k and λ are absorption, extinction coefficients and wavelength.

Extinction spectra of ZnO in Al₂O₃/ZnO nanolaminates, obtained from regression analysis of ellipsometric spectra are shown in Fig. 4. Blue shift of absorption edge and decreasing the extinction peaks were observed with the decrease of nanolaminate bilayer thickness (Fig. 3). The evaluated band gap values E_g were graphically calculated

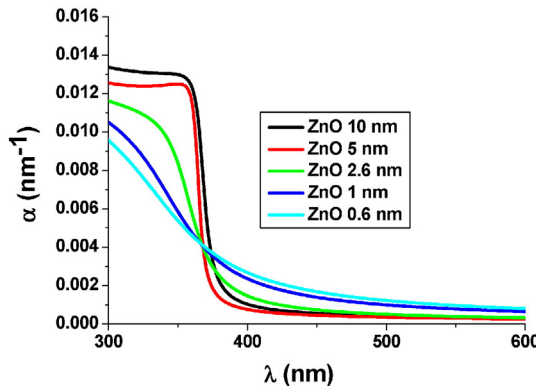


Fig. 4. Absorption spectra of ZnO single layers in Al₂O₃/ZnO nanolaminates with different bilayer thicknesses obtained by calculating from extinction spectra (Fig. 3b).

in linear part of the absorption edge, calculated according to Eq. (2), and summarized in Table 2.

In our previous work [11] we estimated average band gap value for nanolaminates with total thickness of 200 nm and single ZnO layer thickness of 10 nm and 2 nm. These values were 3.36 and 3.45, respectively, therefore the band gap values of ultrathin nanolaminates, grown at the beginning stage are lower than values for the samples with the total thickness 10 times higher.

The absorption edge of the samples lies in the range of 350–400 nm and was sharp for 20 and 10 nm bilayers thickness, meanwhile for 5.2, 2 and 1.2 nm bilayers thickness, the absorption edge was continuous, similar to high surface roughness or amorphous samples. [15]. In order to reveal the structural changes from point of degree of disorder with the decrease of bilayers thickness, the Urbach energy of ZnO was estimated [11]. Urbach tails in absorption peaks are observed when electron from state near the top of valence band is excited to a state near the bottom of conduction band. In the disordered (amorphous) system, electron energy states have different values of those for crystalline (regular) systems. The Urbach energy increases due to the change of the growth of ZnO over Al₂O₃ when the thickness of bilayer decreases from 20 to 1.2 nm. It demonstrates that the number of imperfections increases with the decrease of bilayer spacing and an amorphous structure was formed.

The Urbach tail has been graphically calculated from the linear part of $\ln(\alpha) \sim hv$ plot (Fig. 5). Absorption coefficient obtained from SE data (Fig. 4) have demonstrated that the Urbach tail values increase with the number of bilayers, pointing to the local states into the band gap and to the higher value of disorder [11]. The Urbach tail shows the concentration of local states close to conduction and valence bands.

Additionally, the PL of ultrathin nanolaminates was measured in the range of 365–800 nm and showed no emission for all set of samples. This result could have two possible explanations: (i) Samples are amorphous with not defined grain boundaries. In this case no exciton peaks are expected but defect level emission could be present and (ii) volume-to-surface aspect ratio of the samples is too low. In that case, the surface non radiative recombination is dominant.

Two theories were proposed to explain the results of ultrathin nanolaminates. The first initial idea was based on the growth mechanism proposed by Elam et al. [16] According to Elam et al., the substitution reaction of Zn with Al may happen:



where Zn-OH and Al(C₂H₅)₃ are the substance on the surface and gas phase, correspondently. Due to this reason, the ratio of ZnO can be reduced and doping of ZnO may occur. The ZnO doping with Al was previously discussed by Moret et al. [17], Banerjee et al. [18] and Cheun

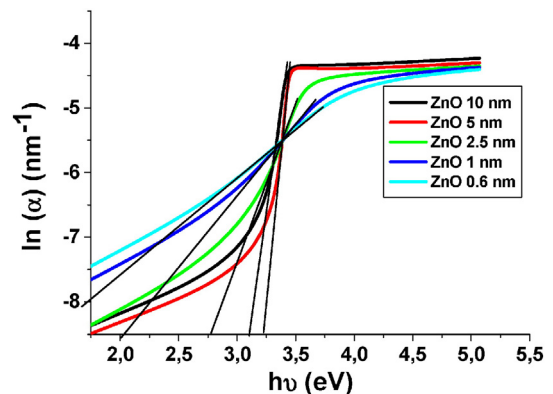


Fig. 5. Calculated Urbach tail from absorption coefficient for ZnO layers.

et al. [19]. The Al doping resulted in the increase of the band gap value and the decrease of ZnO refractive index with the increase of Al doping ratio [20,21]. Comparing the band gap values and the refractive index, we can verify that the decrease of ZnO ratio can be observed only for 1 nm and 0.6 nm layers.

The second way to explain amorphous nature of ultrathin nanolaminates is the minimum thickness required to allow crystallization in a thin film. The proposed crystallization model for ultrathin layers and superlattices is taking into account the interface energies, the thickness of the layers, the melting point of the system, and the bulk amorphous crystallization temperature [22]. It was shown that exponential increase of the crystallization temperature leads to the decrease of the minimal thickness at which crystallization occurs. From XRD and previous HRTEM studies, [12] this bilayer thickness value was shown to be 2.5 nm for Al₂O₃/ZnO nanolaminates. So, we assume that this value is the point at which the crystallization process starts in Al₂O₃/ZnO nanolaminates.

4. Conclusion

In summary, optical and structural properties of ultrathin Al₂O₃/ZnO nanolaminates, deposited on Si and glass substrates have been studied. Regression analysis of ellipsometric spectra have shown that absorption peak decrease and blue shifted with the decrease of bilayers thickness in the stack. Such behavior reveals the formation of disordered structures with decreasing the thickness of bilayers. The degree of disordering has been analyzed by calculating the Urbach tail at the band edge of the absorption spectra of Al₂O₃/ZnO nanolaminates. Analysis of Urbach energy have shown that structures with bilayer spacing of 2 nm and 1.2 nm have noticeably higher Urbach energy values that structures with thicker bilayers thicknesses. The evaluated Urbach energy value of about 0.5 eV and higher for ZnO layer was the indication of the amorphous structure formation. These results were supported by XRD data, no peaks pointing to crystalline structure have been found, as well as the absence of PL excitonic peaks, which was detected in thicker samples [10,11]. Finally, we conclude that on the basis of the analysis of optical methods such as transmission, spectroscopic ellipsometry and photoluminescence of ultrathin nanolaminates, the amorphous nature of them has been proven. These results allowing not only to determine optical properties of Al₂O₃/ZnO nanolaminates but also to get some inside on the formation processes of ultrathin films of Al₂O₃/ZnO.

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